

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14	("5584929" "6549552" "6592663" "6842470").PN. "5868837".pn. "09110576"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 06:48
L2	4	1 and (transistor tft fet mosfet s/d d/s drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 07:03
L3	2777	((257/189,79,E33.003) or (117/952)).CCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/26 06:53
L4	1812	(438/22).CCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/26 06:54
L5	199	3 and 4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 06:54
L6	101	5 and (transistor tft fet mosfet s/d d/s drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 06:55
L7	9	09/590063	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 06:56

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L8	29981	((bulk crystal\$5) near6 (substrate wafer slab)).clm.	US-PGPUB; USPAT	OR	ON	2007/03/26 07:01
L9	4778	(gan gallium adj nitride).clm.	US-PGPUB; USPAT	OR	ON	2007/03/26 07:01
L10	337	L8 same L9	US-PGPUB; USPAT	OR	ON	2007/03/26 07:01
L11	4503	((nitrogen n) with (external outside)).clm.	US-PGPUB; USPAT	OR	ON	2007/03/26 07:01
L12	5	L10 and L11	US-PGPUB; USPAT	OR	ON	2007/03/26 07:33
L13	7416	defect adj density	US-PGPUB; USPAT	OR	ON	2007/03/26 07:03
L14	562	13.clm.	US-PGPUB; USPAT	OR	ON	2007/03/26 07:03
L15	14	10 and 14	US-PGPUB; USPAT	OR	ON	2007/03/26 07:43